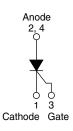


**Vishay Semiconductors** 

# **Thyristor Surface Mount, Phase Control SCR, 16 A**





D<sup>2</sup>PAK (TO-263AB)

PRIMARY CHARACTERISTICS								
I <sub>T(AV)</sub>	16 A							
V <sub>DRM</sub> /V <sub>RRM</sub>	1600 V							
V <sub>TM</sub>	1.25 V							
I <sub>GT</sub>	45 mA							
TJ	-40 °C to +125 °C							
Package	D <sup>2</sup> PAK (TO-263AB)							
Circuit configuration	Single SCR							

### **FEATURES**

- J-STD-020. Meets MSL level 1, per LF maximum peak of 260 °C
- Designed qualified according and JEDEC®-JESD 47
- RoHS Material categorization: COMPLIANT for definitions of compliance please see HALOGEN www.vishay.com/doc?99912 FREE

### **APPLICATIONS**

- Input rectification (soft start)
- Vishay input diodes, switches and output rectifiers which are available in identical package outlines

### DESCRIPTION

The VS-25TTS16SPbF of silicon controlled rectifiers is specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

OUTPUT CURRENT IN TYPICAL APPLICATIONS								
APPLICATIONS	SINGLE-PHASE BRIDGE	THREE-PHASE BRIDGE	UNITS					
NEMA FR-4 or G10 glass fabric-based epoxy with 4 oz. (140 $\mu m)$ copper	3.5	5.5						
Aluminum IMS, R <sub>thCA</sub> = 15 °C/W	8.5	13.5	A					
Aluminum IMS with heatsink, $R_{thCA} = 5 \text{ °C/W}$	16.5	25.0						

### Note

•  $T_A = 55 \text{ °C}, T_J = 125 \text{ °C}, \text{ footprint } 300 \text{ mm}^2$ 

MAJOR RATINGS AND CHARACTERISTICS									
PARAMETER	TEST CONDITIONS	VALUES	UNITS						
I <sub>T(AV)</sub>	Sinusoidal waveform	16	А						
I <sub>RMS</sub>		25	A						
V <sub>RRM</sub> /V <sub>DRM</sub>		1600	V						
I <sub>TSM</sub>		350	A						
V <sub>T</sub>	16 A, T <sub>J</sub> = 25 °C	1.25	V						
dV/dt		500	V/µs						
dl/dt		150	A/µs						
TJ		-40 to +125	°C						

VOLTAGE RATINGS			
PART NUMBER	V <sub>RRM</sub> , MAXIMUM PEAK REVERSE VOLTAGE V	V <sub>DRM</sub> , MAXIMUM PEAK DIRECT VOLTAGE V	I <sub>RRM</sub> ∕I <sub>DRM</sub> , AT 125 °C mA
VS-25TTS16SPbF	1600	1600	10

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<b>ABSOLUTE MAXIMUM RATINGS</b>						
PARAMETER	SYMBOL	BOL TEST CONDITIONS		VAL	UNITS	
FARAMETER	STMDUL	IES	I CONDITIONS	TYP.	MAX.	UNITS
Maximum average on-state current	I <sub>T(AV)</sub>	T <sub>C</sub> = 93 °C, 180° c	onduction half sine wave	1	6	
Maximum RMS on-state current	I <sub>RMS</sub>			2	5	А
Maximum peak, one-cycle,	<b>L</b>	10 ms sine pulse, r	rated V <sub>RRM</sub> applied	30	00	A
non-repetitive surge current	ITSM	10 ms sine pulse, r	no voltage reapplied	3	50	
Maximum I <sup>2</sup> t for fusing	l <sup>2</sup> t	10 ms sine pulse, r	rated V <sub>RRM</sub> applied	4	50	A <sup>2</sup> s
Maximum 1-t for fusing	1-1	10 ms sine pulse, no voltage reapplied			30	
Maximum I²√t for fusing	l²√t	t = 0.1 ms to 10 ms	t = 0.1 ms to 10 ms, no voltage reapplied			
Maximum on-state voltage drop	V <sub>TM</sub>	16 A, T <sub>J</sub> = 25 °C	16 A, T <sub>J</sub> = 25 °C			
On-state slope resistance	r <sub>t</sub>	T <sub>1</sub> = 125 °C		2.0	mΩ	
Threshold voltage	V <sub>T(TO)</sub>	1.0		.0	V	
Maximum reverse and direct lookage autrent	1 /1	T <sub>J</sub> = 25 °C	V roted V A/	0	.5	
Maximum reverse and direct leakage current	I <sub>RM</sub> /I <sub>DM</sub>	T <sub>J</sub> = 125 °C	$V_{R} = rated V_{RRM}/V_{DRM}$	1	0	
Holding current	I <sub>H</sub>	Anode supply = 6 V, resistive load, initial $I_T$ = 1 A, $T_J$ = 25 °C		-	150	mA
Maximum latching current	١L	Anode supply = 6 V, resistive load, $T_J = 25 \ ^{\circ}C$			00	
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J$ max., linear to 80 %, $V_{DRM} = R_g - k = open$		50	00	V/µs
Maximum rate of rise of turned-on current	dl/dt			1	50	A/µs

TRIGGERING					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum peak gate power	P <sub>GM</sub>		8.0	W	
Maximum average gate power	P <sub>G(AV)</sub>		2.0	vv	
Maximum peak positive gate current	+ I <sub>GM</sub>		1.5	А	
Maximum peak negative gate voltage	- V <sub>GM</sub>		10	V	
		Anode supply = 6 V, resistive load, $T_J = -10 \text{ °C}$	60		
Maximum required DC gate current to trigger	I <sub>GT</sub>	Anode supply = 6 V, resistive load, $T_J = 25 \ ^{\circ}C$	45	mA	
		Anode supply = 6 V, resistive load, $T_J = 125 \text{ °C}$	20		
		Anode supply = 6 V, resistive load, $T_J = -10 \degree C$	2.5		
Maximum required DC gate voltage to trigger	V <sub>GT</sub>	Anode supply = 6 V, resistive load, $T_J = 25 \degree C$	2.0	V	
		Anode supply = 6 V, resistive load, $T_J = 125 \text{ °C}$	1.0	V	
Maximum DC gate voltage not to trigger	V <sub>GD</sub>	T 105 °C V Deted volve	0.25		
Maximum DC gate current not to trigger	I <sub>GD</sub>	T <sub>J</sub> = 125 °C, V <sub>DRM</sub> = Rated value	2.0	mA	

SWITCHING								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Typical turn-on time	t <sub>gt</sub>	T <sub>J</sub> = 25 °C	0.9					
Typical reverse recovery time	t <sub>rr</sub>	T - 125 °C	4	μs				
Typical turn-off time	tq	T <sub>J</sub> = 125 °C	110					



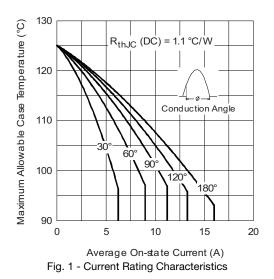
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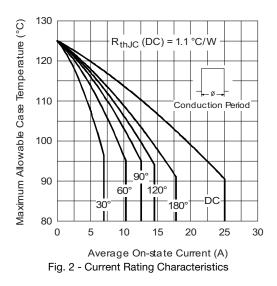
THERMAL AND MECHANICAL SPECIFICATIONS								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-40 to +125	°C				
Soldering temperature	T <sub>S</sub>	For 10 s (1.6 mm from case)	260					
Maximum thermal resistance, junction to case	R <sub>thJC</sub>	DC operation	1.1	°C/W				
Typical thermal resistance, junction to ambient (PCB mount)	R <sub>thJA</sub> <sup>(1)</sup>		40	0/10				
Approvimate weight			2	g				
Approximate weight			0.07	oz.				
Marking device		Case style D <sup>2</sup> PAK (TO-263AB)	25TT	S16S				

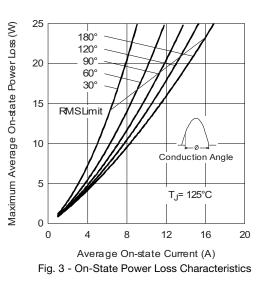
#### Note

<sup>(1)</sup> When mounted on 1" square (650 mm<sup>2</sup>) PCB of FR-4 or G-10 material 4 oz. (140 µm] copper 40 °C/W;

for recommended footprint and soldering techniques refer to application note #AN-994







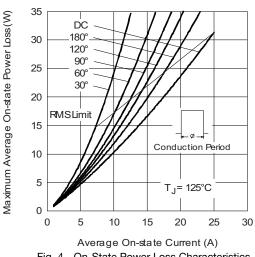


Fig. 4 - On-State Power Loss Characteristics

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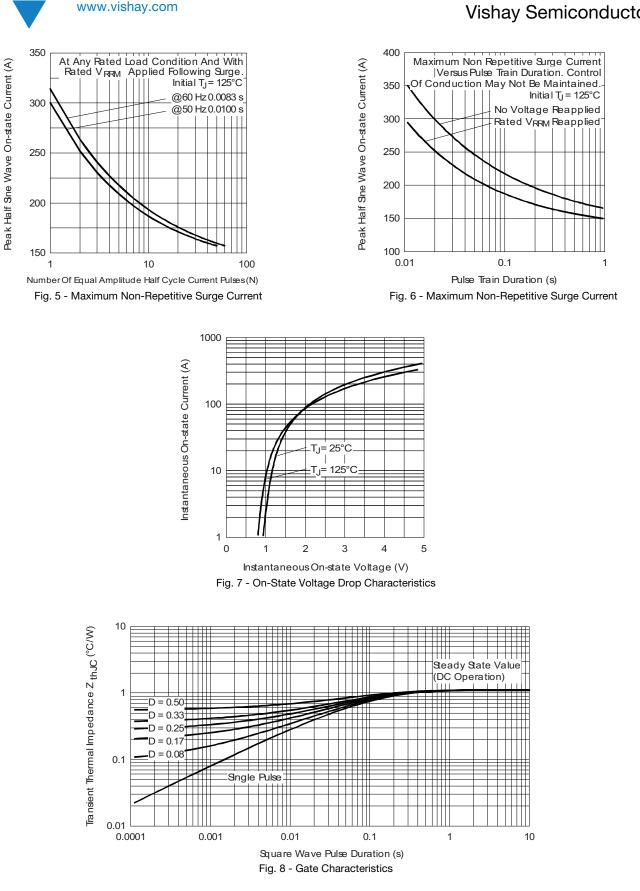
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## VS-25TTS16SPbF

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# VS-25TTS16SPbF

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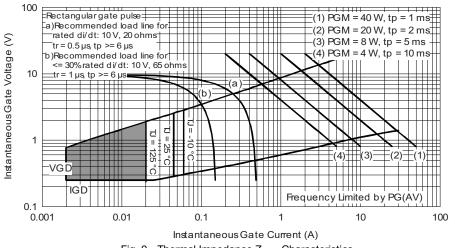


Fig. 9 - Thermal Impedance Z<sub>thJC</sub> Characteristics

### **ORDERING INFORMATION TABLE**

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SHAY

Device code	VS-	25	т	т	S	16	S	TRL	PbF	
	1	2	3	4	5	6	7	8	9	
	1 ·	- Visl	nay Sen	niconduc	ctors pro	oduct				
	2 ·	<ul> <li>Current rating (25 = 25 A)</li> </ul>								
	3		Circuit configuration: T = single thyristor							
	4	- Pac	kage: TO-220							
	5	- Тур	e of silio		erv rect	ifier				
	6			ng: volta	2		= V <sub>RRM</sub>	ı ——	16 = 1	600
	7	- S =	S = TO-220 D <sup>2</sup> PAK (TO-263AB) version							
	8 -	• TF	•	be e and re be and re			'			
	9.	· PbF	= lead	(Pb)-fre	е					

ORDERING INFORMATION (Example)									
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION						
VS-25TTS16SPbF	50	1000	Antistatic plastic tubes						
VS-25TTS16STRRPbF	800	800	13" diameter reel						
VS-25TTS16STRLPbF	800	800	13" diameter reel						

LINKS TO RELATED DOCUMENTS							
Dimensions		www.vishay.com/doc?95046					
Part marking information		www.vishay.com/doc?95054					
Packaging information		www.vishay.com/doc?95032					
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## **Outline Dimensions**



D<sup>2</sup>PAK

### **DIMENSIONS** in millimeters and inches

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SHA



SYMBOL	MILLIM	IETERS	INC	HES	NOTES	NOTES	SYMBOL	MILLIM	IETERS	INC	HES	NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES		STWDUL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010			E	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4		е	2.54	BSC	0.100	BSC	
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110	
С	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4		L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065			L3	0.25 BSC 0.010 BSC				
D	8.51	9.65	0.335	0.380	2		L4	4.78	5.28	0.188	0.208	

#### Notes

<sup>(1)</sup> Dimensioning and tolerancing per ASME Y14.5 M-1994

<sup>(2)</sup> Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

<sup>(3)</sup> Thermal pad contour optional within dimension E, L1, D1 and E1

<sup>(4)</sup> Dimension b1 and c1 apply to base metal only

<sup>(5)</sup> Datum A and B to be determined at datum plane H

<sup>(6)</sup> Controlling dimension: inch

<sup>(7)</sup> Outline conforms to JEDEC<sup>®</sup> outline TO-263AB

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